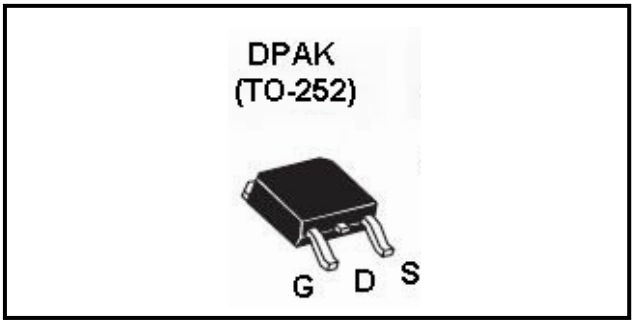
Features

- ♦ Low On-Resistance
- ♦ Fast Switching
- ♦ 100% Avalanche Tested
- ♦ Repetitive Avalanche Allowed up to Tjmax
- ♦ Lead-Free, RoHS Compliant

V_{DS}	30	V
$R_{DS(on),Typ}$	4.0	mΩ
I_D	90	A



Description

VS3080AD designed by the trench processing techniques to achieve extremely low on-resistance. Additional features of this design are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating . These features combine to make this design an extremely efficient and reliable device for use in Motor applications and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only;and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
VGS	Gate-Source Voltage		±20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		30	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_C=25°C	90	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested (Sillicon Limit)	T_C=25°C	320	A
I_D	Continuous Drain current@VGS=10V (See Fig2)	T_C=25°C	90	A
P_D	Maximum Power Dissipation	T_C=25°C	62	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		1.98	°C/W
Drain-Source Avalanche Ratings				
EAS	Avalanche Energy, Single Pulsed ②		225	mJ

Symbol	Parameter		Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)							
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		V_{GS}=0V I_D=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)		V_{DS}=24V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(Tc=125℃)		V_{DS}=24V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current		V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage		V_{DS}=V_{GS},I_D=250μA	0.6	1.2	1.8	V
$R_{DS(ON)}$	Drain-Source On-State Resistance①		V_{GS}=10V, I_D=40A	--	4.0	6.0	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance①		V_{GS}=4.5V, I_D=20A	--	5.5	7.5	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)							
C_{iss}	Input Capacitance		V_{DS}=15V,V_{GS}=0V, f=1MHz	--	1650	--	pF
C_{oss}	Output Capacitance			--	210	--	pF
C_{rss}	Reverse Transfer Capacitance			--	155	--	pF
Q_g	Total Gate Charge	V_{GS}=10V	V_{DS}=15V,I_D=20A, V_{GS}=10V	--	36	--	nC
		V_{GS}=4.5V			18.5		nC
Q_{gs}	Gate-Source Charge			--	5	--	nC
Q_{gd}	Gate-Drain Charge			--	8	--	nC
Switching Characteristics							
$t_{d(on)}$	Turn-on Delay Time		V_{DD}=15V, I_D=10A, R_G=6.8Ω, V_{GS}=10V	--	13.5	--	nS
t_r	Turn-on Rise Time			--	15	--	nS
$t_{d(off)}$	Turn-Off Delay Time			--	20	--	nS
t_f	Turn-Off Fall Time			--	14	--	nS
Source- Drain Diode Characteristics@ T_J = 25°C (unless otherwise stated)							
I_{SD}	Source-drain current(Body Diode)		T_C=25℃	--	--	90	A
V_{SD}	Forward on voltage		I_{SD}=60A,V_{GS}=0V	--	--	1.3	V
t_{rr}	Reverse Recovery Time		T_j=25℃,I_{sd}=30A, V_{GS}=0V di/dt=100A/μs	--	24	--	nS
Q_{rr}	Reverse Recovery Charge				13	--	nC

NOTE:

① Pulse width ≤ 300μs; duty cycle≤ 2%.

② Limited by Tjmax, starting TJ = 25°C, L = 0.5mH,RG = 25Ω, IAS = 30A, VGS =10V.

Part not recommended for use above this value

③ Repetitive rating; pulse width limited by max. junction temperature.

Typical Characteristics

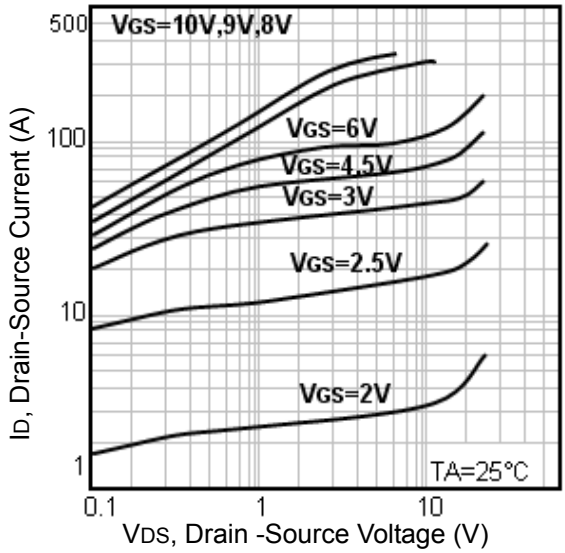


Fig1. Typical Output Characteristics

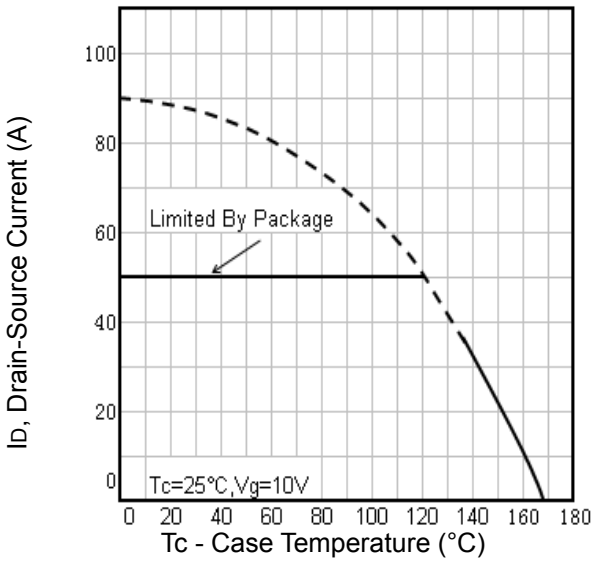


Fig2. Maximum Drain Current Vs.Case Temperature

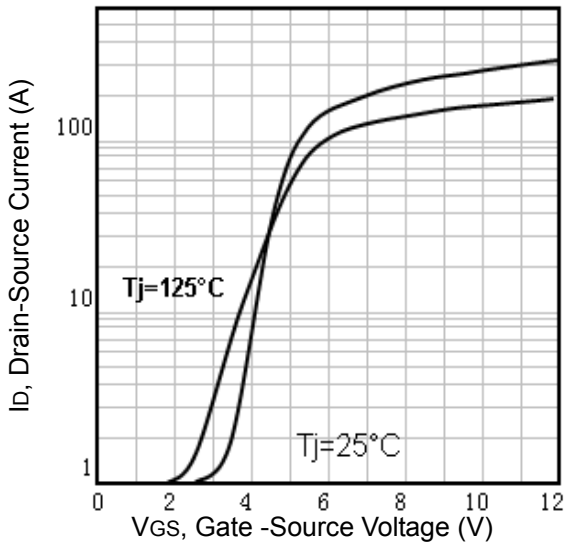


Fig3. Typical Transfer Characteristics

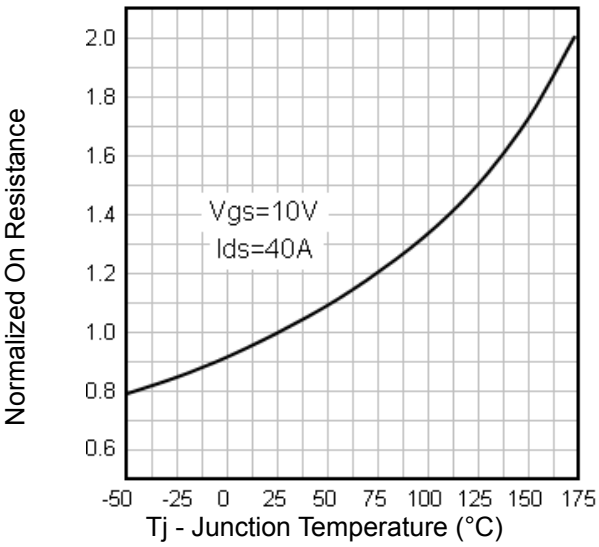


Fig4. Normalized On-Resistance Vs. Temperature

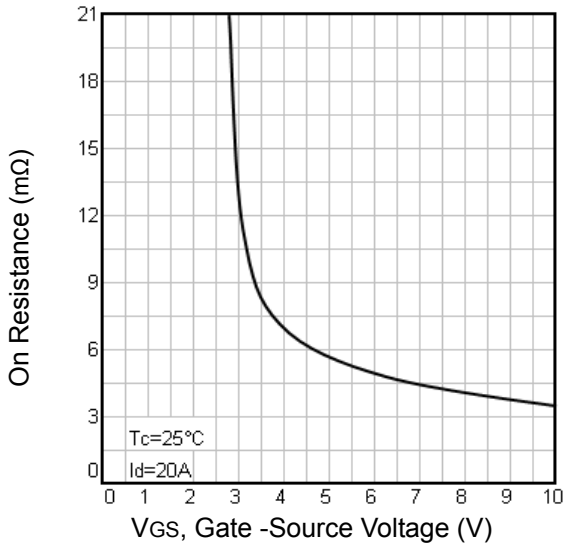


Fig5. On Resistance Vs. Gate -Source Voltage

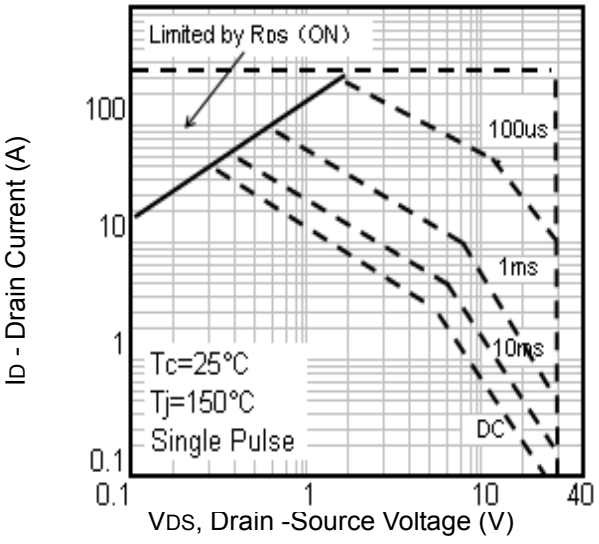


Fig6. Maximum Safe Operating Area

Typical Characteristics

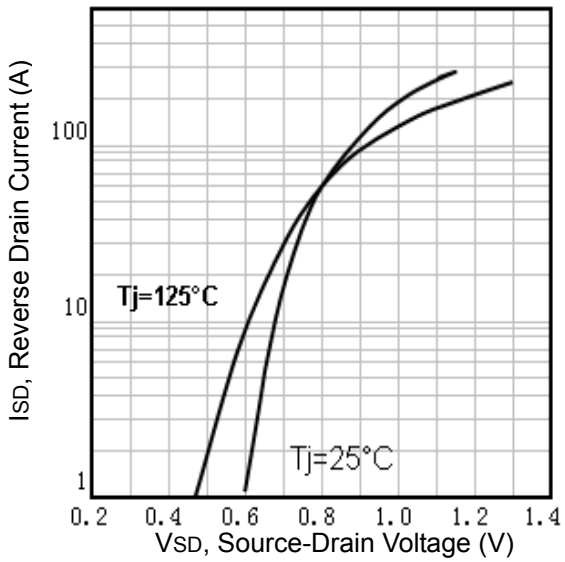


Fig7. Typical Source-Drain Diode Forward Voltage

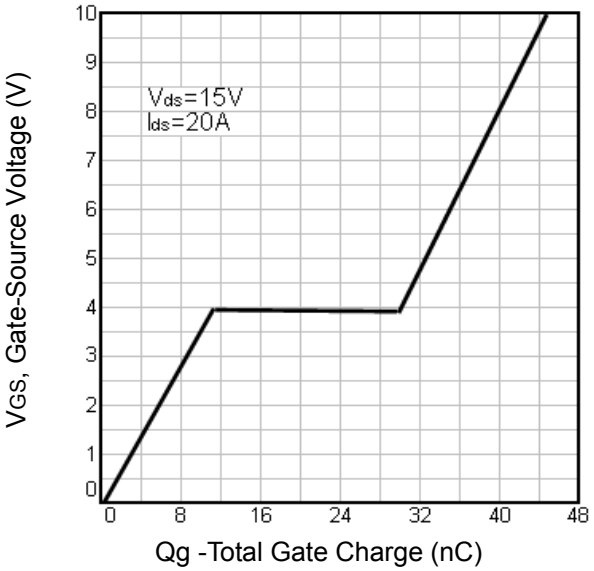


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

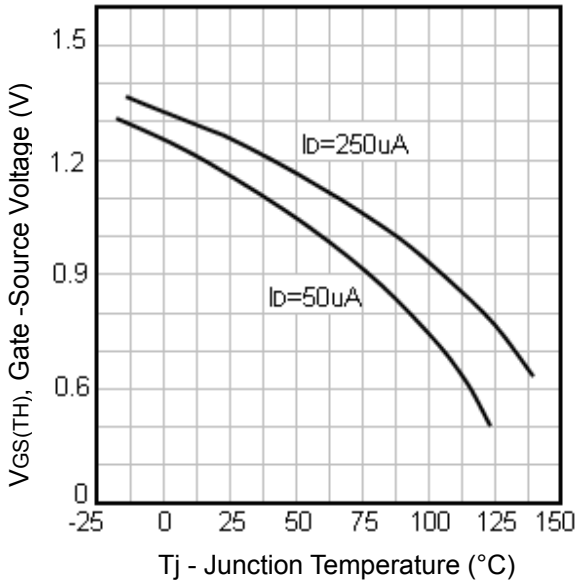


Fig9. Threshold Voltage Vs. Temperature

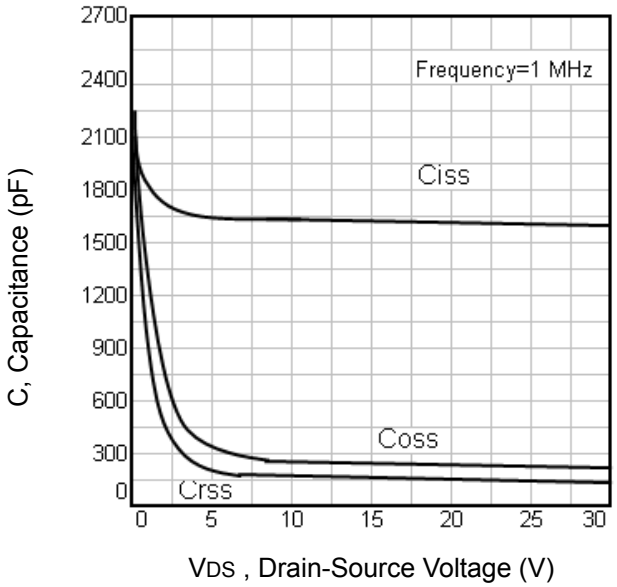


Fig10. Typical Capacitance Vs.Drain-Source Voltage

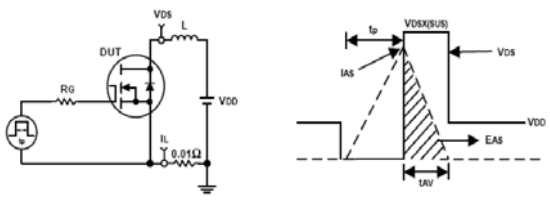


Fig11. Unclamped Inductive Test Circuit and waveforms

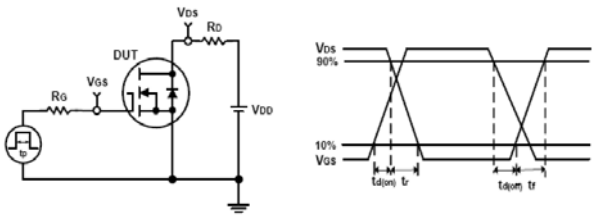
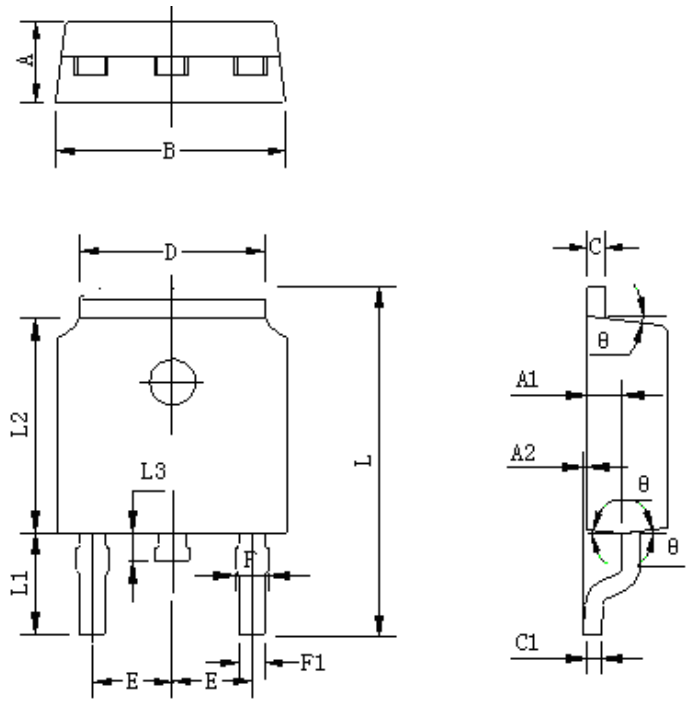


Fig12. Switching Time Test Circuit and waveforms

TO-252 Package Outline



TO-252 Dimensions (Unit:mm)

Symbol	Min	Nom	Max
A	2.25	2.3	2.35
A1	0.96	1.01	1.06
A2	0.05	0.10	0.15
B	6.05	6.60	6.65
C	0.46	0.508	0.580
C1	0.508	0.508	0.508
D	5.31	5.32	5.33
E	2.186	2.286	2.386
F	0.075	0.085	0.095
F1	0.660	0.76	0.860
L	9.80	9.825	10.40
L1	2.9REF		
L2	6.05	6.10	6.15
L3	0.79	0.80	0.81
θ	7°	7°	7°

Marking

Logo
Product Name & Package Code
XXX：Product Lot Code
YWW：Year and week Code

Order Information

Product	Package	Packaging	Min Unit Quantity
VS3080AD	TO-252	2500PCS/Reel	5000PCS

Customer Service

Sales and Service:
sales@vgsemi.com
Shen Zhen Vangaurd Semiconductor CO., LTD
TEL: (86-755) -26902410
FAX: (86-755) -26907027
WEB: www.vgsemi.com